Abstract

A semiconductor device has a first semiconductor die and a first insulating layer formed over the first semiconductor die. A trench is formed in the first insulating layer. A second insulating layer is formed over the first insulating layer. A recess forms in the second insulating layer over the trench automatically as part of the formation process of the second insulating layer. A second semiconductor die is mounted over the second insulating layer. The recess completely surrounds the second semiconductor die in plan view. An underfill is dispensed between the first semiconductor die and second semiconductor die.

(Fig. 2l)